DB151S THRU DB157S

General Purpose Bridge Rectifier

Features

- $I_{F(AV)}$ 1.5A
- V_{RRM} 50V-1000V
- High surge current capability
- Glass passivated chip

Applications

- General purpose 1 phase Bridge rectifier applications

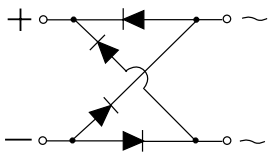
Marking

- DB15XS

  X：From 01 To 7

DBS





Limiting Values (Absolute Maximum Rating)

Item	ymbol	Unit	Conditions		DB15						
					1S	2S	3S	4S	5S	6S	7S
Repetitive Peak Reverse Voltage	V_{RRM}	V			50	100	200	400	600	800	1000
Maximum RMS Voltage	V_{RMS}	V			35	70	140	280	420	560	700
Average Rectified Output Current	I_O	A	60Hz sine wave, R-load ,Ta=25℃	On glass-epoxi substrate	1.5						
Surge(Non-repetitive)Forward Current	I_{FSM}	A	60Hz half sine wave, 1 cycle, T_j=25℃		60						
Current Squared Time	I^2t	A^2S	1ms≤t<8.3ms Tj=25℃， Rating of per diode		15						
Operation Junction and Storage Temperature Range	T_J,T_{stg}	℃			-55 ~+150						

Electrical Characteristics（T_a=25℃ Unless otherwise specified）

Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	V_{FM}	V	I_{FM}=1.5A, Pulse measurement, Rating of per diode	1.1
Peak Reverse Current	I_{RRM}	μA	V_{RM}=V_{RRM} , Pulse measurement, Rating of per diode	10
Thermal Resistance	$R_{\theta J-A}$	℃/W	Between junction and ambient, On glass-epoxi substrate	68
	$R_{\theta J-L}$		Between junction and lead	15

Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

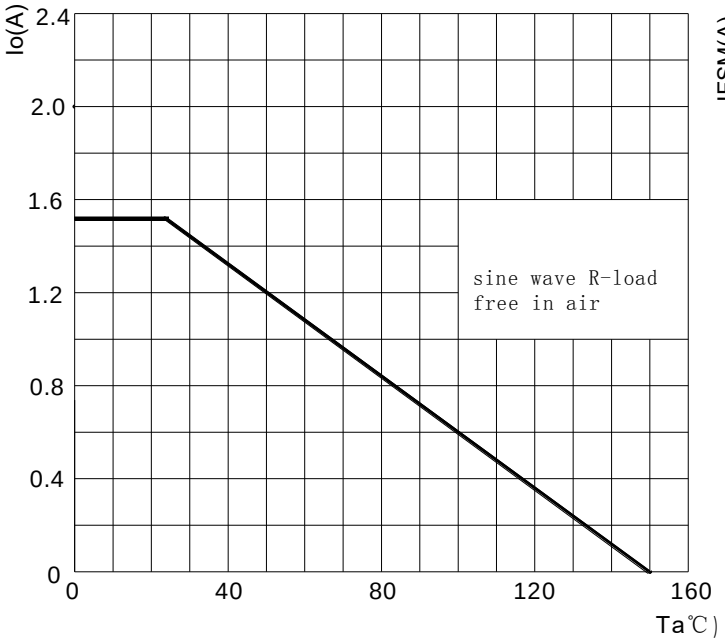


FIG.2:MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

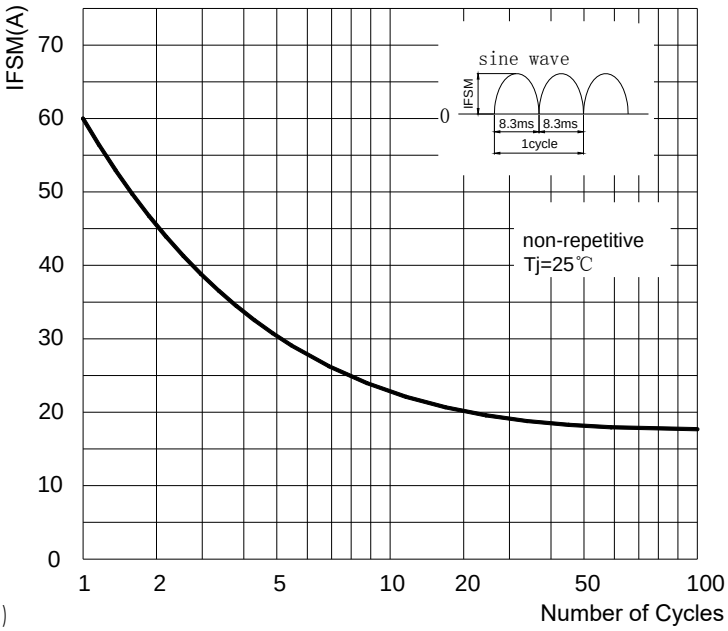


FIG.3: TYPICAL FORWARD CHARACTERISTICS

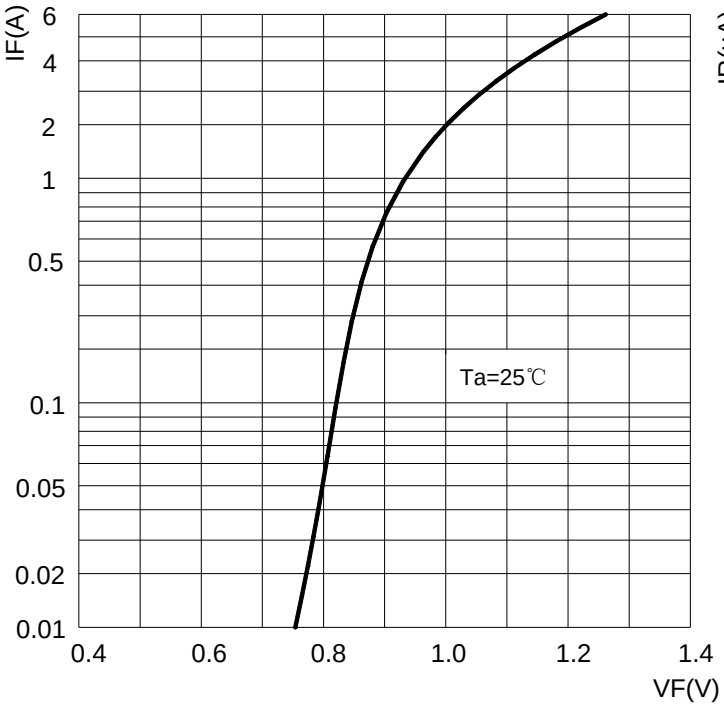
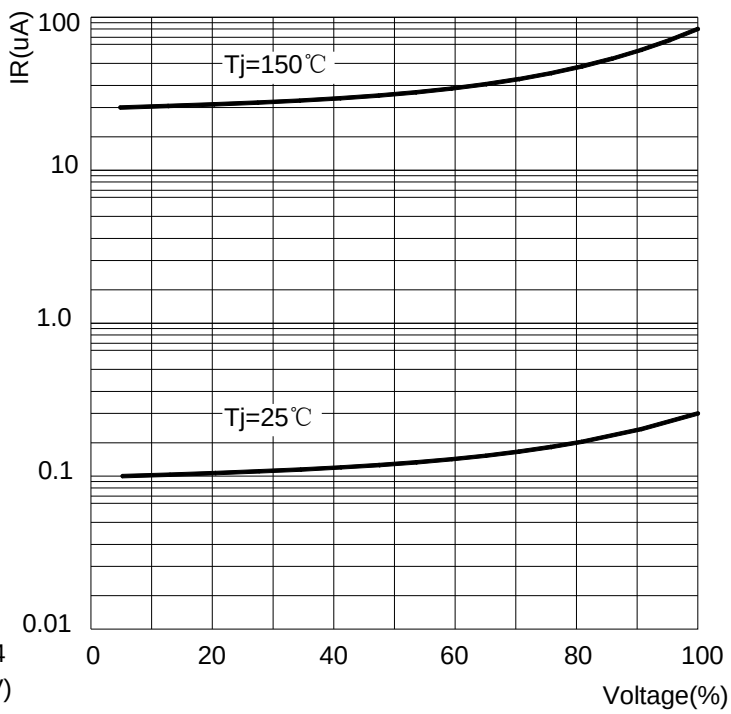
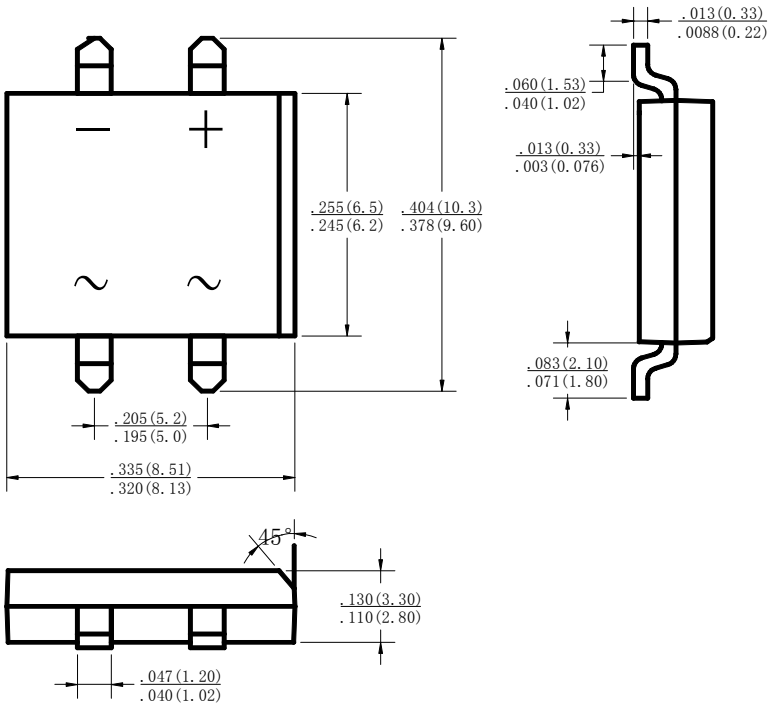


FIG.4:TYPICAL REVERSE CHARACTERISTICS

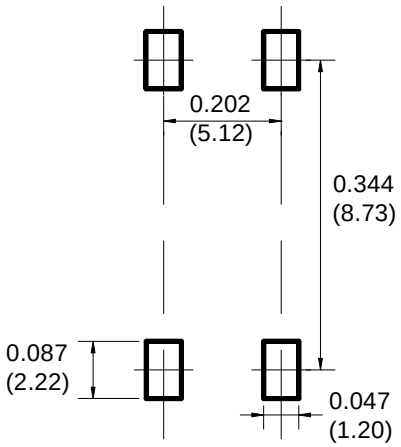


DBS Package Outline Dimensions



Dimensions in inches and (millimeters)

DBS Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.